IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No
Filing Date July 17, 1998
Inventor J. Dennis Keller et al.
Assignee Micron Technology, Inc.
Group Art Unit
Examiner M. Estrada
Attorney's Docket No
Title: Methods of Forming Floating Gate Transistors, and Floating Gate Transistors

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Reference - - See attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the references listed on the attached Form PTO-1449. No admission is made regarding whether the submitted references are prior art.

Citation of these references are respectfully requested.

Respectfully submitted,

Date:

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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE						ATTY. DOCKET MI22-587		SERIAL NO. 09/118,359			
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)											
	AR	AR H. Shirai, et al., A 0.54µm ² Self-Aligned, HSG Floating Gate Cell (SAHF Cell) for 256Mbit Flash Memories, 1995 IEEE pp27.1.1-27.1.4									
	AS	Yosiaki S. Hisamune 2.3.4	Yosiaki S. Hisamune et al, A High Capacitive-Coupling Ratio (HiCR) Cell for 3 V-Only 64 Mbit and Future Flash Memories, 1993 IEEE pp2.3.1-2.3.4								
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.											